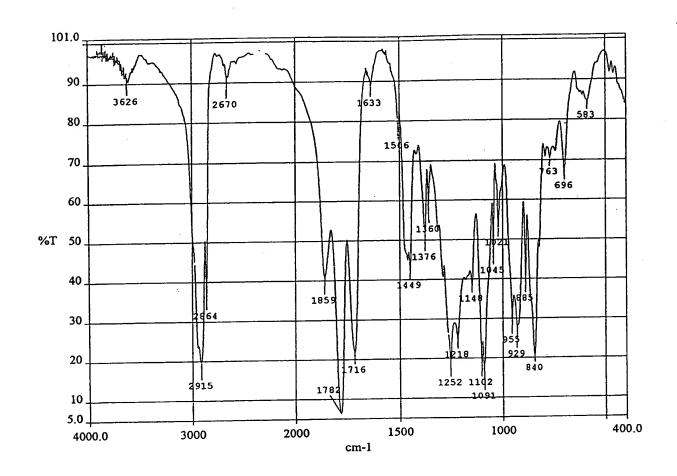
SMZM&S Ref. No.: SMZM&S Tel. No.:

Q65210 (202) 293-7060 ASPECT RATIO

Sheet 1 of 2





042815-2.PK

042815-2.SP 3601 4000.0 400.0 6.3 100.0 4.0 %T 8 3.0

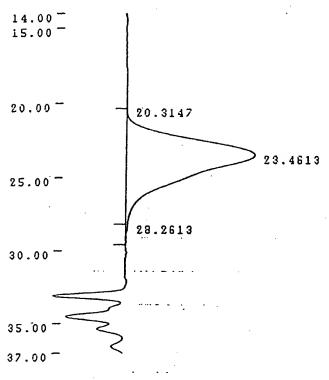
REF 4000 97.0 2000 88.8 600 3626.9 90.1 2915.5 19.9 2864.1 37.9 2670.0 91.1 1859.1 40.8 1782.3 6.3 1716.3 21.7 1633.7 88.8 1506.0 77.5 1449.8 42.9 1376.8 52.2 1360.3 57.1 1252.0 19.5 1218.2 25.2 1148.3 38.4 1102.8 18.0 1091.1 18.3 1045.0 48.6 1021.6 52.9 955.2 30.1 929.9 27.9 885.8 39.9 840.0 20.6 763.8 70.4 696.1 66.9 583.4 84.7

Inventor Name: Taeko IDEGAWA et al.
of Invention: NOVEL COPOLYMER, PHOTORESIST COMPOSITION,
PROCESS FOR FORMING RESIST PATTERN WITH ASPECT I I ASPECT RATIO

Filing Date: July 11, 2001 SMZM&S Ref. No.: SMZM&S Tel. No.:

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FIG. 2



CHANNEL 1 METHOD 0,0,4,3

CALIBRATION OFF

NO. NAME	RET TIME	AREA	MARK	I	D#	CONC	CONC %
1	20.3147	96.1	М	I	1	96.1277	0.0042
2 ·	23.4613	2280773.8	М	I	2	2280773.7500	99.6871
3	28.2613	7062.7	М	I	3	7062.6992	0.3087
TOTAL		2287932.8				2287932.5770	100.0000

CALIBRATION DATA

3 ORDER REGRESSION

LOG M = $a*T^3+b*T^2+c*T^1+d$

a = -6.509859E-004 _....

b = 5.063016E-002

c = -1.552977E+000 d = 2.123975E+001

- PEAK	TOP	RT	= 23.	5750 ::	· M· =	17299
MM	i =		11243	•		
M k] =		18729	MW/MN	=	1.8858

MZ = 27080 MZ/MN = 2.4087